

READING FLASH MEMORY

ABSTRACT OF THE DISCLOSURE

5 A method and system for reading flash memory. A leakage current of a common bit line comprising the flash memory cell is accessed. A read current of the flash memory cell is accessed. The leakage current is eliminated from the read current to determine a cell current. The cell current is compared to an erase verify cell current. The currents may be directly subtracted, or they may be converted to corresponding voltages and the voltages subtracted. Advantageously, cells may be correctly verified for erasure without a preliminary
10 search and recovery of over erased bits. As a beneficial result, the search and recovery of over erased bits does not need to be performed during an erase process. Advantageously, such steps may be eliminated from an erase process, recovering the time otherwise required to perform such steps, and thereby speeding up the erase process.